L Number	Hits	Search Text	DB	Time stamp
1	1874	simulat\$3 same wafer	USPAT;	2003/07/01 18:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2	(circulates and surface) and (turnature many allipida)	IBM_TDB	2002/07/04 46:27
2	2	(simulat\$3 same wafer) same (tungsten near silicide)	USPAT;	2003/07/01 16:27
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	92	(simulat\$3 same wafer) same (test near wafer)	USPAT:	2003/07/01 16:27
		(US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	5	(simulat\$3 same wafer) same ((test near wafer) same	USPAT;	2003/07/01 16:32
		(standard near2 wafer))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	E.C.	(/tast many wafer) same (standard many) wafer))	IBM_TDB	2003/07/01 16:33
5	56	((test near wafer) same (standard near2 wafer))	USPAT; US-PGPUB;	2003/07/01 10:33
			EPO; JPO;	:
			DERWENT;	
			IBM_TDB	
6	256260	(photoresist or polymer or resin) same (silicon or tantalum or	USPAT;	2003/07/01 16:36
1		nickel or aluminum or tungsten)	US-PGPUB:	7.3
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	6434	((photoresist or polymer or resin) same (silicon or tantalum or	USPAT;	2003/07/01 16:37
ŀ		nickel or aluminum or tungsten)) same bak\$3	US-PGPUB;	(16.1) The same of
			EPO; JPO;	
			DERWENT;	
	12	////nhatarasiat ar nalymar ar rasin) sama (silisan ar tantalym ar	IBM_TDB USPAT;	2002/07/04 46:42
9	12	((((photoresist or polymer or resin) same (silicon or tantalum or nickel or aluminum or tungsten)) same bak\$3) same	US-PGPUB;	2003/07/01 16:43
		simulat\$3) same simulat\$3	EPO; JPO;	
		Similarity of Same Similarity	DERWENT;	
			IBM_TDB	
10	7	(((((photoresist or polymer or resin) same (silicon or tantalum	USPAT;	2003/07/01 16:43
		or nickel or aluminum or tungsten)) same bak\$3) same	US-PGPUB;	
		simulat\$3) same simulat\$3) and @pd<19990331	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/07/04 47 40
8	12	(((photoresist or polymer or resin) same (silicon or tantalum or	USPAT;	2003/07/01 17:13
		nickel or aluminum or tungsten)) same bak\$3) same simulat\$3	US-PGPUB;	,
			EPO; JPO; DERWENT;	
			IBM_TDB	
11	1838	(coat\$3 or deposit\$3) same ((mixture or combination) same	USPAT;	2003/07/01 17:23
''	1030	(silicon and photoresist))	US-PGPUB;	2300/01/01 17.20
İ		(Simon and priories asset))	EPO; JPO;	7
			DERWENT;	
1			IBM_TDB	
12	5	((coat\$3 or deposit\$3) same ((mixture or combination) same	USPAT;	2003/07/01 17:17
ĺ		(silicon and photoresist))) and (simulat\$3 same wafer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
10		(100 1 1 1100)	IBM_TDB	0000/07/04 10 5=
13	340	(coat\$3 or deposit\$3) same ((mixture or combination) same	USPAT;	2003/07/01 18:27
		(silicon near5 photoresist))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
		L	ם חו דואוחי	L

14	1	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same simulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/01 17:29
15	0	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same alouminum)	IBM_TDB USPAT; US-PGPUB;	2003/07/01 17:30
16	54	//cpat/C2 or democit/C2) come //windows are a shire time)	EPO; JPO; DERWENT; IBM_TDB	
10	54	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/01 17:33
17	29	(((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and (wafer same aluminum)) and @pd<19990331	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/01 17:34
18	181	((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/01 18:30
19	1	(((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331) and (simulat\$3 same wafer)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/07/01 18:29
20	0	(((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist))) and @pd<19990331) and 428/698-702.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/01 18:30
21	27856	(simulat\$3 or calibrat\$3 or test\$3) same wafer	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/01 18:36
22	40	((simulat\$3 or calibrat\$3 or test\$3) same wafer) and ((coat\$3 or deposit\$3) same ((mixture or combination) same (silicon near5 photoresist)))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/01 18:36
-	1863	simulat\$3 same wafer	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/01 16:11
-	24	(simulat\$3 same wafer) same (photoresist same silicon)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/25 20:54
-	12	((simulat\$3 same wafer) same (photoresist same silicon)) and @pd<19990331	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/06/25 20:56
-	0	(simulat\$3 same wafer).clms.	EPO; JPO; DERWENT; IBM_TDB	2002/00/00 00 00
			USPAT; US-PGPUB	2003/06/26 20:38
-	105	(simulat\$3 same wafer).clm.	USPAT; US-PGPUB	2003/06/26 20:39
-	32	((simulat\$3 same wafer).clm.) and @pd<19990331	USPAT; US-PGPUB	2003/06/26 20:40